

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Previously Presented) A method of introducing impurity; wherein, in the course of introducing a material to a solid substance which has an oxidized film or other film sticking on the surface,

the oxidized film and other film are first removed as the surface treatment to the solid substance with a means for dipping the surface or the solid substance in a reductive liquid,

a certain desired particle is attached or introduced;

wherein the reductive liquid is at least one liquid selected from the group consisting of sulfinic acid and adipic acid di-2-ethylhexyl ester.

2. - 4. (Cancelled)

5. (Previously Presented) The method of introducing impurity recited in claim 1, wherein

the means for dipping the surface of solid substance in a reductive liquid rubs the surface of the solid substance mechanically when the solid substance is dipped in the reductive liquid.

6. (Original) The method of introducing impurity recited in claim 1, wherein

the certain desired particle is attached or introduced by bringing a gas containing the certain desired particle to make contact to the surface of solid substance which surface has been made to be free of the oxidized film and other film, thereby the particle is attached or introduced to the surface, or the vicinity, of solid substance.

7. (Previously Presented) The method of introducing impurity recited in claim 1, wherein

the certain desired particle is attached or introduced by irradiating the surface of the solid substance, which surface has been made to be free of the oxidized film and other film, with an electromagnetic wave whose energy matches the energy that is binding the hydrogen or hydroxyl radical sticking on the surface with the atom of the solid substance, thereby converting the binding into a non-coupled state, separating the sticking hydrogen or hydroxyl radical, and exposing the atom constituting the solid substance to the surface; and then introducing the certain desired particle for making contact so that the particle is attached or introduced to the surface, or the vicinity, of the solid substance.

8. (Previously Presented) The method of introducing impurity recited in claim 7, wherein

the energy of the irradiating electromagnetic wave is greater than 318 kJ/mol and less than 666 kJ/mol.

9. (Previously Presented) The method of introducing impurity recited in claim 8, wherein

the energy of the irradiating electromagnetic wave is 425 kJ/mol or higher.

10. (Previously Presented) The method of introducing impurity recited in claim 1, wherein

the attaching or introducing of the certain desired particle is conducted in an environment in which the temperature of the solid substance is lower than 600°C.

11. (Previously Presented) A method of introducing impurity; wherein, in the course of introducing a material in the phase of ion, plasma, or gas, to a solid substance which has an oxidized film or other film sticking to the surface,

the oxidized film and other film are first removed as the surface treatment to solid substance with means for dipping the surface of solid substance in a reductive liquid, and then

a certain desired particle is attached or introduced;

wherein the reductive liquid is at least one liquid selected from the group consisting of sulfinic acid and adipic acid di-2-ethylhexyl ester.

12. (Original) The method of introducing impurity recited in claim 1, wherein the certain desired particle is attached or introduced while it is in either one of the states among plasma, gas and ultra low-energy ion.

13. (Original) The method of introducing impurity recited in claim 1, wherein at least one facility selected from among each of the following respective categories is used; at least one apparatus selected from among the group consisting of an apparatus for irradiating the surface of solid substance with plasma, an apparatus for irradiating the surface of solid substance with gas and an apparatus for dipping the surface of solid substance in a reductive liquid; an apparatus for bringing a gas containing a certain desired particle to the surface of solid substance; and an annealing apparatus for diffusing the certain desired particle attached or introduced therein.

14. (Original) The method of introducing impurity recited in claim 13, wherein the apparatus for dipping the surface of solid substance in a reductive liquid is provided with a mechanism for rubbing the surface of solid substance mechanically.

15. (Cancelled)

16. (Original) The method of introducing impurity recited in claim 13, wherein at least two items selected from among the following categories are used in a combination mode or as an integration; at least one apparatus selected from among the group consisting of an apparatus for irradiating the surface of solid substance with plasma, an apparatus for irradiating the surface of solid substance with gas and an apparatus for dipping the surface of solid substance in a reductive liquid; an apparatus for bringing a gas containing a certain desired particle to make contact with the surface of solid substance; and an annealing apparatus for diffusing the certain desired particle attached or introduced therein.

17. - 50. (Cancelled)